**R20** 

Code No: **R204104U** 

Set No. 1

# IV B.Tech I Semester Regular Examinations, January – 2024 BASIC ELECTRONICS

(Common to All Branches except ECE)

Time: 3 hours Max. Marks: 70 Answer any FIVE Questions ONE Question from Each unit All Questions Carry Equal Marks UNIT - I a) Illustrate the concepts of insulator, semiconductor & conductor with help of 1 energy band structure. [7] b) Explain the V-I Characteristics of a diode. [7] a) Describe the application of a diode as a Half-Wave Rectifier. 2 [7] b) Elucidate the need of a filter and Regulator after the rectification process. [7] **UNIT - II** 3 a) Explain the Zener diode V-I characteristics. [7] b) Discuss the applications of Zener diode. [7] (OR) a) What is varactor diode? Summarize the characteristics. 4 [7] b) Interpret the working principle of optical diode with neat sketches. [7] UNIT - III a) Make use of transistor CE configuration to explain input, output characteristics 5 and various regions of the configuration in detail. [7] What is the need for transistor biasing? Explain atleast one type of biasing techniques with neat circuit diagram? [7] (OR) 6 Distinguish the various configurations of transistor. [7] a) Explicit the application of transistor as a switch. [7] **UNIT - IV** 7 a) Compare the performance of FET with BJT. [7] b) Discuss the FET Common Drain Amplifier. [7] a) Elucidate the characteristics and parameters of JFET. 8 [7] b) Illustrate the drain and transfer characteristics of depletion type MOSFET. [7] UNIT - V 9 a) Discuss the principle of operation and characteristics of Thyristors. [7] b) Describe the applications of Silicon-Controlled Rectifier. [7] (OR) 10 a) Explain the concept of UJT. [7] Discuss the process of light activated SCR. [7]

# **R20**

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Set No. 2

### IV B.Tech I Semester Regular Examinations, January – 2024

#### **BASIC ELECTRONICS**

(Common to All Branches except ECE)

Time: 3 hours Max. Marks: 70 Answer any FIVE Questions ONE Question from Each unit All Questions Carry Equal Marks \*\*\*\* UNIT - I a) Compare the energy band diagram of metals, insulators and semi-conductor. [7] Explain the diode biasing and also the diode V-I characteristics. [7] (OR) 2 Distinguish Half-Wave and Full-Wave Rectifiers. a) [7] b) Elucidate the steps for AC to DC conversion. [7] UNIT - II What is Zener diode? How it is different from a basic diode, compare in all 3 a) [7] aspects. b) Discuss how the Zener diode acts as a voltage regulator. [7] (OR) a) Explain the characteristics of varactor diode. 4 [7] b) Illustrate the characteristics of optical diode. [7] UNIT - III 5 a) Explicate the structure and operation of basic transistor. [7] b) Discuss the characteristics and parameters of transistor. [7] Explain the various transistor configurations. 6 a) [7] b) Explicit the application of transistor as an amplifier. [7] **UNIT-IV** 7 a) Write the advantages of JFET. Also compare with BJT. [7] b) Describe the operation of common drain JFET amplifier and derive the equation for voltage gain. [7] (OR) a) Elucidate the characteristics of JFET. 8 [7] b) Compare JFET with MOSFET. [7] UNIT - V 9 a) Discuss the principle of operation and characteristics of SCR. [7] b) Describe two applications of Silicon-Controlled Rectifier. [7] (OR) 10 a) Draw the equivalent circuit of UJT and also discuss the characteristics. [7] b) What is the need of optical coupler and explain the concept with neat sketches. [7]

Code No: R204104U R20

Set No. 3

## $IV\ B. Tech\ I\ Semester\ Regular\ Examinations,\ January-2024$

#### **BASIC ELECTRONICS**

(Common to All Branches except ECE)

Time: 3 hours Max. Marks: 70 Answer any FIVE Questions ONE Question from Each unit All Questions Carry Equal Marks \*\*\*\* UNIT - I Illustrate theFermi level in intrinsic and extrinsic semiconductor materials. [7] 1 Explain the concept of biasing a diode. What are different diode models? [7] 2 Illustrate briefly about power supply filters. a) [7] Describe the need and types of regulators. [7] UNIT - II Distinguish Zener diode and PN junction diode in all aspects. 3 [7] a) Discuss atleast two applications of Zener diode in detail. [7] a) How varactor diode is different from PN diode. Explain its characteristics. 4 [7] Interpret the different types and applications of optical diode. [7] UNIT - III Make use of transistor CB configuration and discuss its input and output 5 characteristics in Detail. [7] b) What is thermal Runaway in transistor? Explain the method to overcome it. [7] (OR) a) Discuss the input and outputcharacteristics of a transistor. 6 [7] b) Explicit atleast two applications of transistor. [7] **UNIT - IV** Compare JFET with BJT. a) [7] Describe the Common Source amplifier with neat diagram. [7] (OR) a) Elucidate the different types of JFET basing. 8 [7] b) Explain the characteristics of MOSFET. [7] UNIT - V What is the need of a 4-layer device? Discuss the principle of operation of SCR 9 a) with neat figure. [7] b) Draw the equivalent circuit of UJT and also discuss the characteristics. [7] Write the advantages of UJT. Distinguish UJT and BJT. 10 [7] Explain the need of photo transistor and also discuss the concept with neat circuit diagram. [7]

#### IV B.Tech I Semester Regular Examinations, January – 2024 BASIC ELECTRONICS

(Common to All Branches except ECE)

Time: 3 hours Max. Marks: 70 Answer any FIVE Questions ONE Question from Each unit All Questions Carry Equal Marks \*\*\*\* UNIT - I a) Give the mathematical analysis and show that the Fermi energy level lies in the 1 centre of forbidden energy band for an intrinsic semiconductor. [7] b) Describe the terms intrinsic and extrinsic semiconductors of both P type and N type. [7] (OR) a) Elucidate the application of a diode as a Full-Wave Rectifier. 2 [7] b) What is the need of a filter after the rectifier? Classify them. [7] UNIT - II 3 a) Compare Zener diode and PN junction diode in all aspects. [7] b) Explain how the Zener diode acts as a voltage regulator. [7] (OR) 4 a) Illustrate the characteristics of varactor diode. [7] b) Interpret the different types and applications of optical diode. [7] UNIT - III a) With suitable sketches, explain input and output characteristics of CC 5 Configuration in detail. [7] b) What is Transistor biasing? Explain about fixed bias Technique. [7] (OR) a) Discuss the parameters of a transistor. 6 [7] b) Explain Transistor acting as an amplifier with neat sketches. [7] **UNIT - IV** 7 a) Distinguish JFET performance with BJT. [7] b) Draw the circuit diagram of a Common Source amplifier circuit and explain the importance of each component. [7] (OR) 8 a) Draw the small signal model of JFET. [7] b) Discuss the MOSFET parameters. [7] UNIT - V a) Explain the need of a Thyristor. Discuss the principle of operation and 9 characteristics of Thyristor with neat circuit diagram. [7] b) Explain the concept of UJT with neat sketches. [7] (OR)10 a) List the advantages of UJT. Compare UJT performance with BJT. [7] b) What is the need of insulated gate BJT and explain the concept with neat circuit diagram. [7]